

1990 Index

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This index covers all items — papers, correspondence, reviews, etc. — that appeared in this periodical during 1990, and items from previous years that were commented upon or corrected in 1990.

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- defect cluster analysis for wafer-scale integration; redundant-circuit yield prediction. *Pukiite, Paul R.*, +, *T-SEM Aug 90* 128-135

- redundant metal-polyimide thin-film interconnection process for wafer-scale dimensions. *Michalka, Timothy L.*, +, *T-SEM Nov 90* 158-167

Wiring; cf. Integrated-circuit interconnections

Y

Yield optimization

- AC product defect level and yield loss for logic and RAM chips. *Savir, Jacob*, *T-SEM Nov 90* 195-205
 calculating defect densities from single data set and expressing in units of defects per geometric factor per independent variable. *Comeau, Alain*, *T-SEM May 90* 84-88
 cluster-modified Poisson model for estimating defect density and yield. *Ferris-Prabhu, Albert V.*, *T-SEM May 90* 54-59
 defect cluster analysis for wafer-scale integration; redundant-circuit yield prediction. *Pukiite, Paul R.*, +, *T-SEM Aug 90* 128-135
 development and refinement of net-die-per-wafer yield models over last 25 years. *Cunningham, James A.*, *T-SEM May 90* 60-71
 edge passivation and related electrical stability in silicon power devices. *Salkalachen, S.*, +, *T-SEM Feb 90* 12-17
 hypothesis testing technique for determining difference in sampled defective parts using Fisher's exact test. *Hackerott, Michael*, +, *T-SEM Nov 90* 247-248
 test-chip-based approach to automated diagnosis of CMOS yield problems. *Lukaszek, Wes*, +, *T-SEM Feb 90* 18-27
 yield model applicable when some chip defect repairs are possible. *Michalka, Timothy L.*, +, *T-SEM Aug 90* 116-127

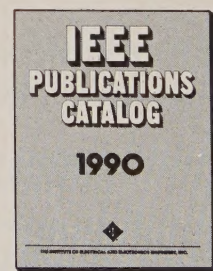
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